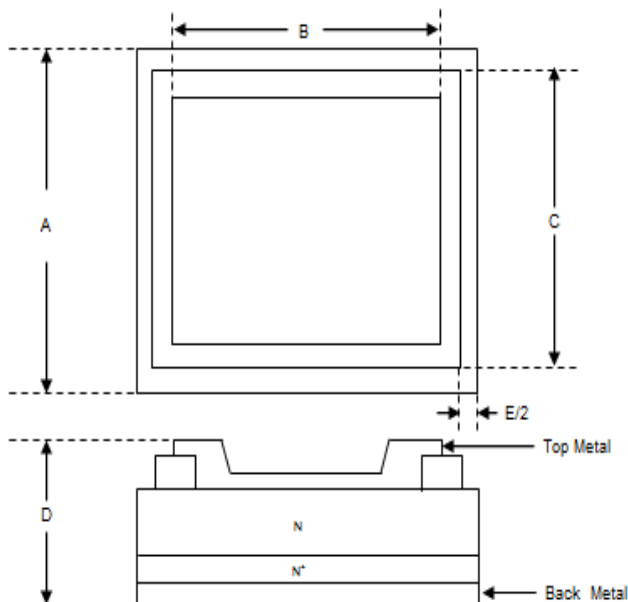


Planar Schottky Barrier Diode Wafer (PSBD)



| Item | Dimensions | |
|------------------------|------------|------|
| | um | mil |
| Die Size (A) | 2362 | 93 |
| Top Metal Pad Size (B) | 2282 | 89.8 |
| Passivation Seal (C) | 2302 | 90.6 |
| Wafer Thickness (D) | 260 | 10.2 |
| Scribe Line Width (E) | 60 | 2.36 |
| Other Informations | | |
| Wafer Size | 6" | |
| Gross Die | 2856 | |
| Top Metal | Ag | |
| Back Metal | Ag | |

Electrical Characteristics @TA=25°C

| Item | Symbol | Spec. Limit | Die Sort | Unit |
|---|-----------|-------------------|----------------|---------|
| Maximum Repetitive Peak Reverse Voltage @0.05mA | V_{RRM} | 200 | 210 | V |
| Maximum Average Forward Rectified Current | I_o | 15 | - | A |
| Forward Voltage Drop, @ $I_F=3A$ @ $I_F=10A$ @ $I_F=15A$ | V_F | - 0.87 0.92 | 0.76 - - | V |
| Maximum Reverse Current at Rated V_{RRM} | I_R | 3 | 1 | μA |
| Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method) | I_{FSM} | 220 | - | A |
| Operating Temperature Range | T_J | -50 to +175 | - | °C |
| Storage Temperature Range | T_{STG} | -50 to +175 | - | °C |